



Keys to your expectation in Optics

Dilase 750

Fully modular high-end direct laser lithography system

- ▶ An advanced system for very high resolution
- ▶ Flexible and fully customizable
- ▶ 266nm, 325nm, 375nm, 405nm or 445nm
- ▶ Compatible with all photoresists
- ▶ Very high aspect ratio : 1x50
- ▶ Fast patterning and mask fabrication
- ▶ Large writing exposure area

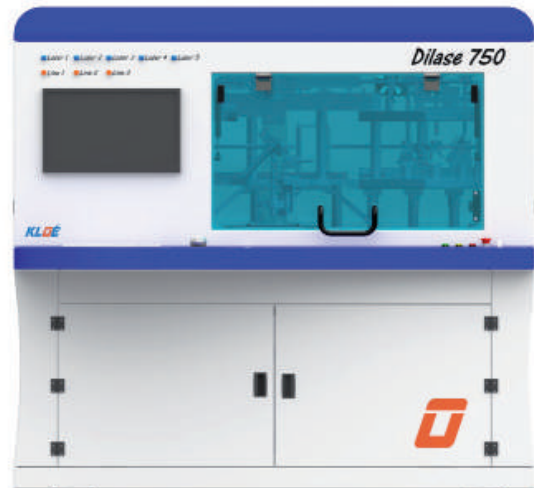


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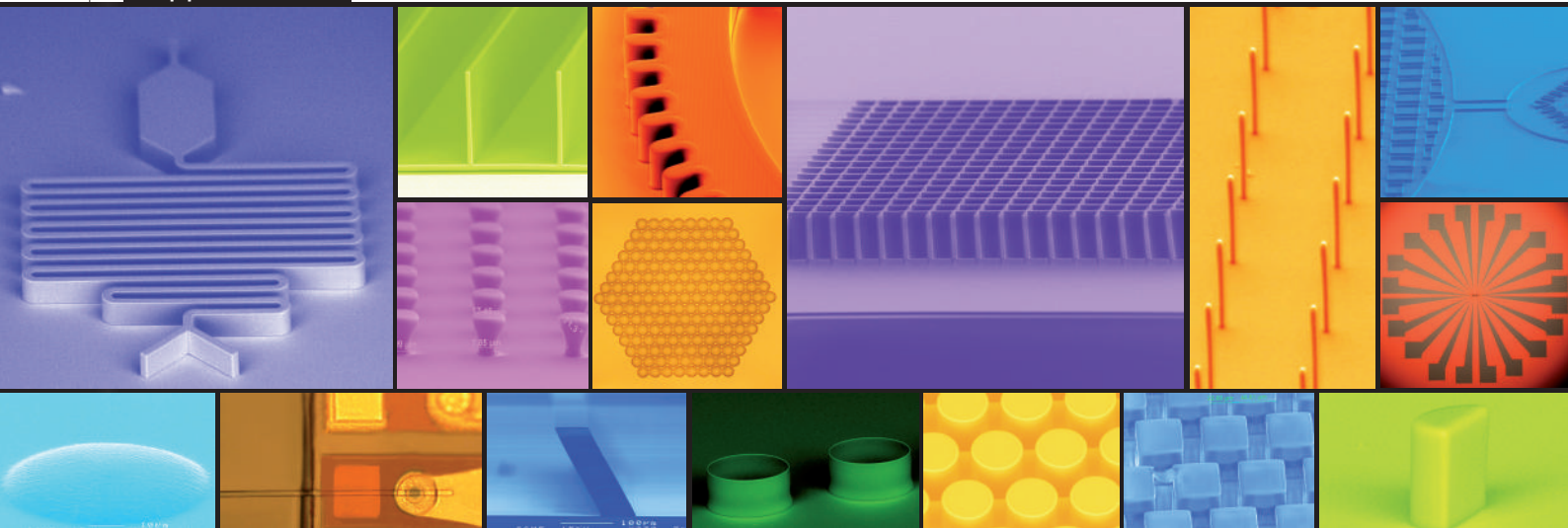
Dilase 750 is a high-end and fully customizable high-resolution laser lithography equipment. This complete direct laser processing system writes patterns in layers of blue or ultraviolet photosensitive materials. One or more (until 3) fixed sources can be installed at available wavelengths of 266 nm, 325 nm, 375 nm, 405 nm or 445 nm. The exposure surface can be extended up to 12 inches, with a standard maximum trajectory deviation of 100 nm. The different optical sub-assemblies offer several laser spot size options, all the way down to 500 nm wide. This high performance system is totally custom-made, to fit the specific prototyping or manufacturing needs of customers. Dilase 750 is compatible with most commercially available photoresists, such as SU8, Shipley and AZ resins. It is merely optimized for use with the K-CL resin developed by Kloé for fine resolution and high aspect ratio lithographic applications (1x50) or microfluidic devices fabrication.

Features

- Size : 1801 x 1204 x 1790 mm
- Integrated computer control interfaces (MS Windows based / windows OS)
- 1 or 3 laser sources : 266, 325, 375, 405 or 445 nm
- 1 to 3 optical sub-assemblies
- High resolution video positioning system
- Data formats supported : LWI (Kloé Software format), DXF, GDS2
- Automated focusing setting
- Integrated design software : Kloé Design V.2
- 3 modes of write : vectorial, raster scan and combination of both.



Applications



Performances

Linear writing speed	> 350 mm.s ⁻¹
Stage travel resolution	40 nm - 100 nm
Repeatability	100 nm
Wafer writing area	5 mm to 12 inches
Substrate thickness	250 µm to 10 mm
Laser spot size (1 or 2)	0.5 µm to 100 µm
Form factor	Minimum 10
Realignment precision	500 nm